

## ZXGD3103N8

### SYNCHRONOUS MOSFET CONTROLLER

## Description

The ZXGD3103 is intended to drive MOSFETS configured as ideal diode replacements. The device is comprised of a differential amplifier detector stage and high current driver. The detector monitors the reverse voltage of the MOSFET such that if body diode conduction occurs a positive voltage is applied to the MOSFET's Gate pin.

Once the positive voltage is applied to the Gate the MOSFET switches on allowing reverse current flow. The detectors' output voltage is then proportional to the MOSFET Drain-Source reverse voltage drop and this is applied to the Gate via the driver. This action provides a rapid turn off as current decays.

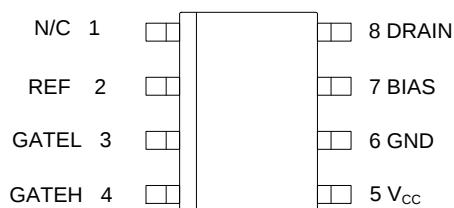
## Features

- Proportional Gate Drive
- Turn-off propagation delay 15ns and turn-off time 20ns.
- Detector threshold voltage ~10mV
- Standby current 5mA
- Suitable for Discontinuous Mode (DCM), Critical Conduction Mode (CrCM) and Continuous Mode (CCM) operation
- 5-15V V<sub>CC</sub> range

## Applications

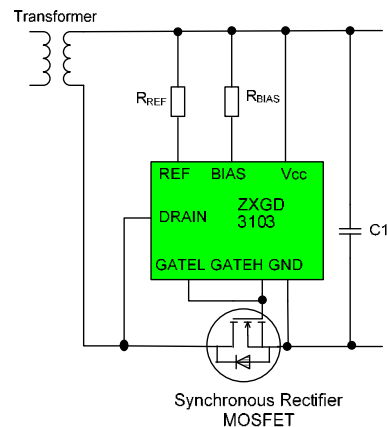
- Flyback Converters in:
  - Adaptors
  - LCD Monitors
  - Server PSU's
  - Set Top Boxes
  - LCD TV
- Resonant Converters
  - LED TV
  - High power Adaptors
  - Street Lighting
  - ATX psu

## Pin out details



**SO-8**

## Typical Configuration



## Ordering information

| Device       | Status     | Package | Part Mark | Reel size (inches) | Tape width (mm) | Quantity per reel |
|--------------|------------|---------|-----------|--------------------|-----------------|-------------------|
| ZXGD3103N8TC | Production | SO8     | ZXGD3103  | 13                 | 12              | 2500              |

### Absolute maximum ratings

| Parameter                                     | Symbol       | Limit              | Unit             |
|-----------------------------------------------|--------------|--------------------|------------------|
| Supply voltage <sup>1</sup>                   | $V_{CC}$     | 15                 | V                |
| Continuous Drain pin voltage <sup>1</sup>     | $V_D$        | -3 to 180          | V                |
| GATEH and GATEL output Voltage <sup>1</sup>   | $V_G$        | -3 to $V_{CC} + 3$ | V                |
| Driver peak source current                    | $I_{SOURCE}$ | 2.5                | A                |
| Driver peak sink current                      | $I_{SINK}$   | 6                  | A                |
| Reference current                             | $I_{REF}$    | 25                 | mA               |
| Bias voltage                                  | $V_{BIAS}$   | $V_{CC}$           | V                |
| Bias current                                  | $I_{BIAS}$   | 100                | mA               |
| Power dissipation at $T_A = 25^\circ\text{C}$ | $P_D$        | 490                | mW               |
| Operating junction temperature                | $T_j$        | -40 to +150        | $^\circ\text{C}$ |
| Storage temperature                           | $T_{stg}$    | -50 to +150        | $^\circ\text{C}$ |

Notes: 1. All voltages are relative to GND pin.

### Thermal resistance

| Parameter               | Symbol          | Value | Unit               |
|-------------------------|-----------------|-------|--------------------|
| Junction to ambient (a) | $R_{\theta JA}$ | 255   | $^\circ\text{C/W}$ |
| Junction to lead (b)    | $R_{\theta LA}$ | 120   | $^\circ\text{C/W}$ |

Notes: a. Mounted on minimum 1oz weight copper on FR4 PCB in still air conditions.  
b. Output Drivers - Junction to solder point at end of the lead 5 and 6

### ESD Rating

| Model      | Rating | Unit |
|------------|--------|------|
| Human Body | 4000   | V    |
| Machine    | 400    | V    |

**ZXGD3103N8**

 Electrical characteristics at  $T_A = 25^\circ\text{C}$ ;  $V_{CC} = 10\text{V}$ ;  $R_{BIAS} = 3.3\text{k}\Omega$ ;  $R_{REF} = 4.3\text{k}\Omega$ 

| Parameter                        | Symbol              | Conditions                     | Min. | Typ. | Max. | Unit |
|----------------------------------|---------------------|--------------------------------|------|------|------|------|
| Input and supply characteristics |                     |                                |      |      |      |      |
| Operating current                | I <sub>OP</sub>     | V <sub>D</sub> ≤ -200m V       | -    | 2.16 | -    | mA   |
|                                  |                     | V <sub>D</sub> ≥ 0V            | -    | 5.16 | -    |      |
| Gate Driver                      |                     |                                |      |      |      |      |
| Turn-off Threshold Voltage(**)   | V <sub>T</sub>      | V <sub>G</sub> = 1V, ( * )     | -16  | -10  | 0    | mV   |
| GATE output voltage (**)         | V <sub>G(off)</sub> | V <sub>D</sub> ≥ 0V, ( * )     | -    | 0.73 | 1    | V    |
|                                  | V <sub>G</sub>      | V <sub>D</sub> = -50mV, ( † )  | 6.0  | 7.2  | -    |      |
|                                  |                     | V <sub>D</sub> = -100mV, ( † ) | 8.8  | 9.2  | -    |      |
|                                  |                     | V <sub>D</sub> ≤ -150mV, ( † ) | 9.2  | 9.4  | -    |      |
|                                  |                     | V <sub>D</sub> ≤ -200mV, ( † ) | 9.3  | 9.5  | -    |      |

 Switching performance (") for  $Q_{G(tot)} = 82\text{nC}$ 

|                            |          |                                        |  |     |  |    |
|----------------------------|----------|----------------------------------------|--|-----|--|----|
| Turn on Propagation delay  | $t_{d1}$ | Refer to switching waveforms in Fig. 3 |  | 150 |  | ns |
| Turn off Propagation delay | $t_{d2}$ |                                        |  | 15  |  |    |
| Gate rise time             | $t_r$    |                                        |  | 450 |  |    |
| Gate fall time             | $t_f$    | Continuous Conduction Mode             |  | 21  |  |    |
|                            |          | Discontinuous Conduction Mode          |  | 17  |  |    |

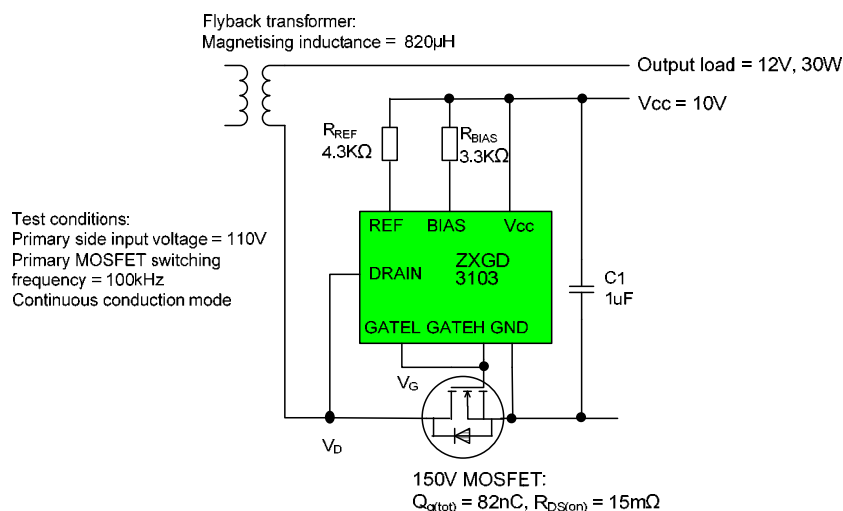
**Notes:**

(\*\*) GATEH connected to GATEL

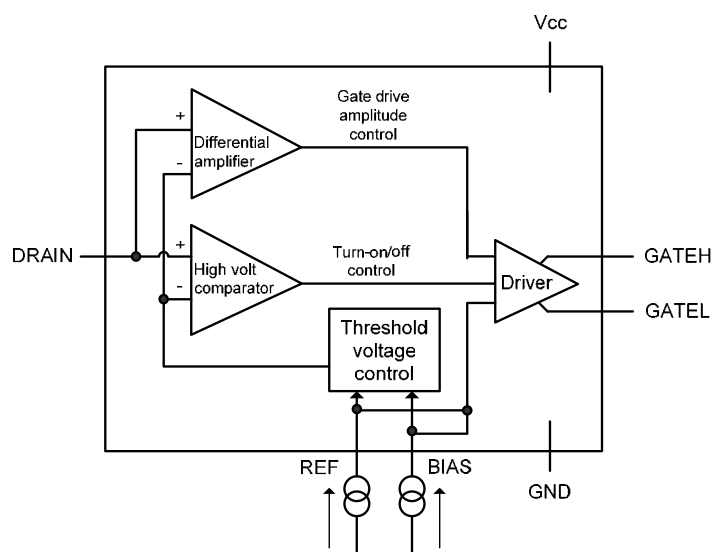
 (\*)  $R_H = 100\text{k}\Omega$ ,  $R_L = \text{O/C}$ 

 (†)  $R_L = 100\text{k}\Omega$ ,  $R_H = \text{O/C}$ 

(") refer to test circuit below

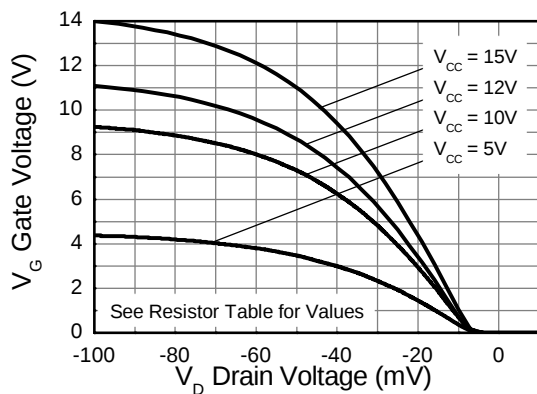


### Schematic Symbol and Pin Out Details

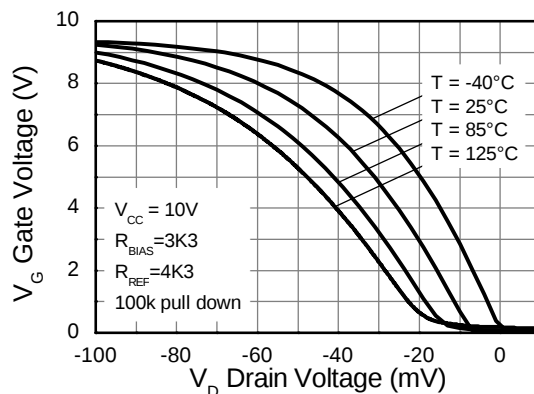


| Pin No. | Name     | Description and function                                                                                                            |
|---------|----------|-------------------------------------------------------------------------------------------------------------------------------------|
| 1       | NC       | <b>No Internal connection</b>                                                                                                       |
| 2       | REF      | <b>Reference</b><br>This pin is connected to $V_{CC}$ via resistor, $R_{REF}$ .                                                     |
| 3       | GATEL    | <b>Gate turn off</b><br>This pin sinks current, $I_{SINK}$ , from the synchronous MOSFET Gate.                                      |
| 4       | GATEH    | <b>Gate turn on</b><br>This pin sources current, $I_{SOURCE}$ , to the synchronous MOSFET Gate.                                     |
| 5       | $V_{CC}$ | <b>Power Supply</b><br>This is the supply pin. It is recommended to decouple this point to ground closely with a ceramic capacitor. |
| 6       | GND      | <b>Ground</b><br>This is the ground reference point. Connect to the synchronous MOSFET Source terminal.                             |
| 7       | BIAS     | <b>Bias</b><br>This pin is connected to $V_{CC}$ via resistor, $R_{BIAS}$ .                                                         |
| 8       | DRAIN    | <b>Drain connection</b><br>This pin connects directly to the synchronous MOSFET Drain terminal.                                     |

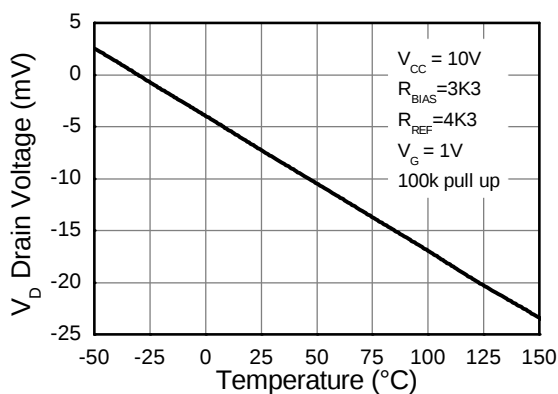
## Typical Characteristics



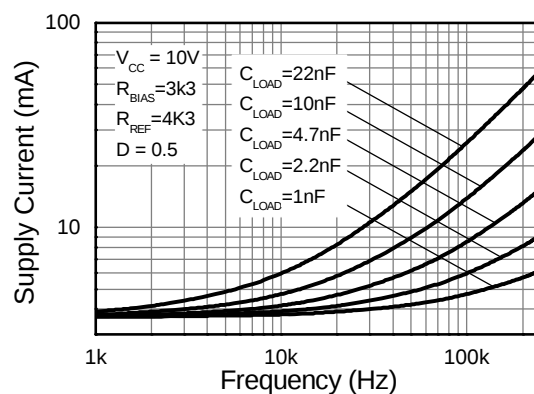
Transfer Characteristic



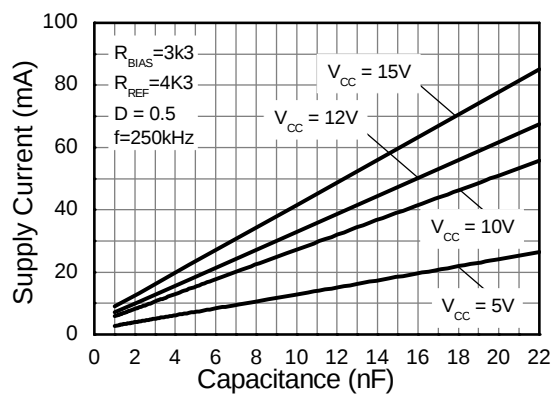
Transfer Characteristic



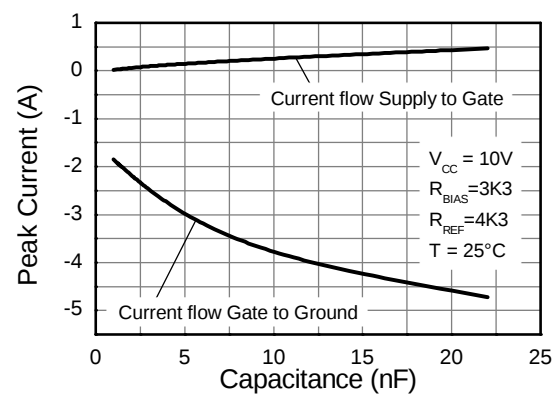
Drain Sense Voltage vs Temperature



Supply Current vs Frequency

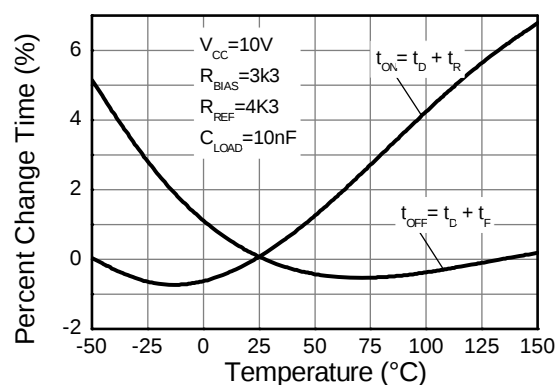
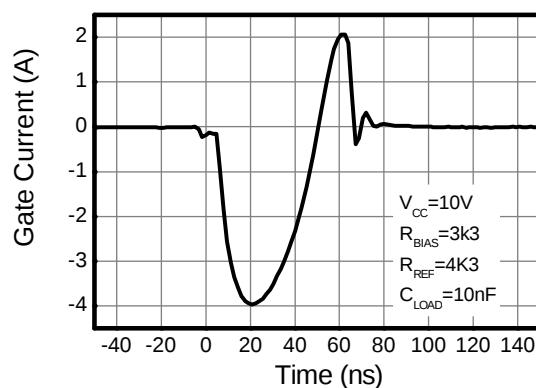
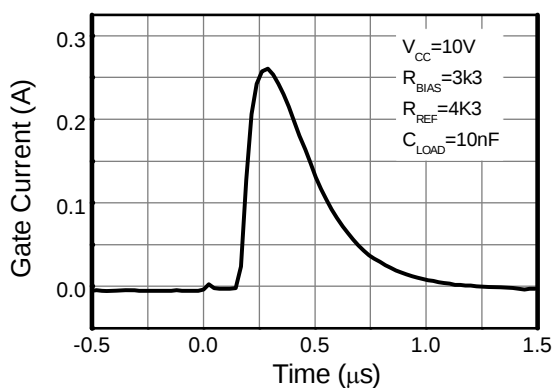
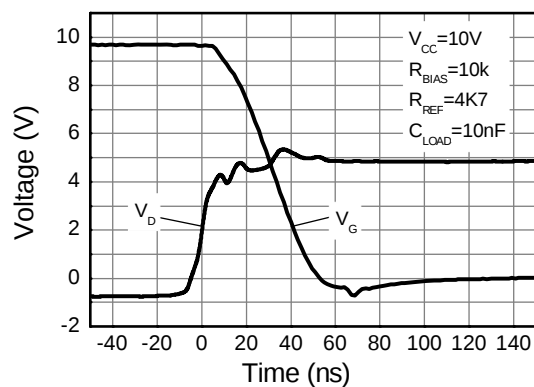
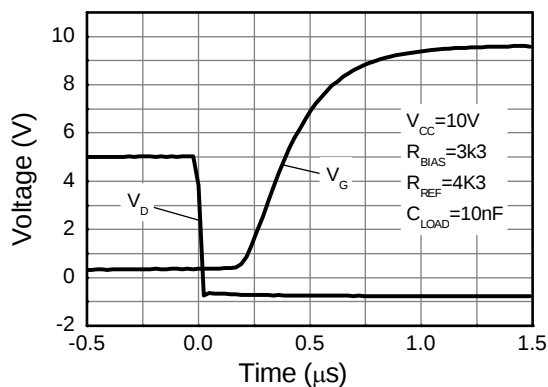


Supply Current vs Capacitive Load



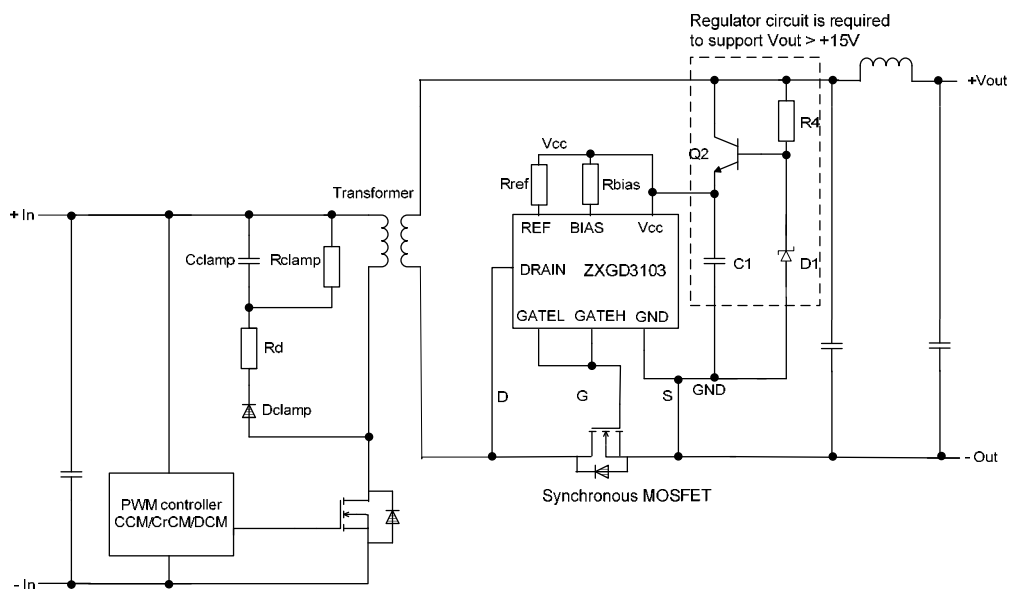
Gate Current vs Capacitive Load

## Typical Characteristics

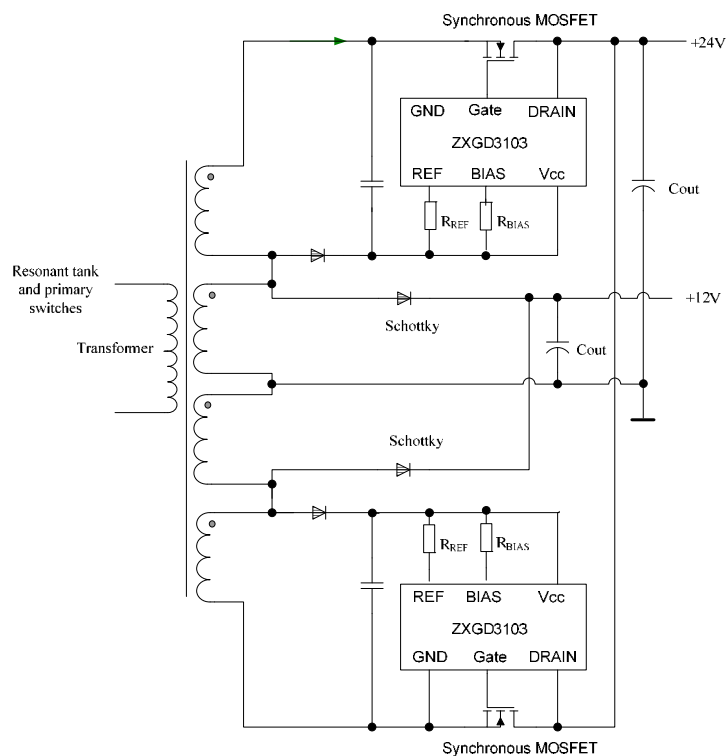


## Application information

The purpose of the ZXGD3103 is to drive a MOSFET as a low- $V_F$  Schottky diode replacement in offline power converters. When combined with a low  $R_{DS(ON)}$  MOSFET, it can yield significant power efficiency improvement, whilst maintaining design simplicity and incurring minimal component count. Figure 1 and 2 show typical configuration of ZXGD3103 for synchronous rectification in a Flyback and a multiple output resonant converter.



**Figure 1. Example connections in Flyback supply**



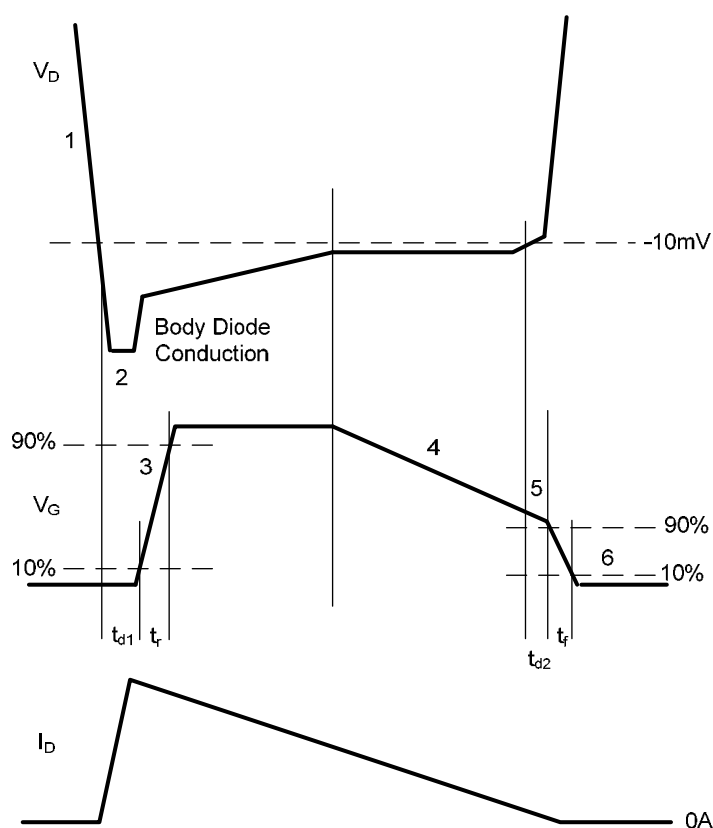
**Figure 2. Example connections in LLC supply**

## Descriptions of the normal operation

The operation of the device is described step-by-step with reference to the timing diagram in Figure 3.

1. The detector monitors the MOSFET Drain-Source voltage.
2. When, due to transformer action, the MOSFET body diode is forced to conduct there is approximately -0.8V on the Drain pin.
3. The detector outputs a positive voltage with respect to ground, this voltage is then fed to the MOSFET driver stage and current is sourced out of the GATE pin.
4. The controller goes into proportional gate drive control — the GATE output voltage is proportional to the on-resistance-induced Drain-Source voltage drop across the MOSFET. Proportional gate drive ensures that MOSFET conducts for majority of the conduction cycle and minimizes body diode conduction time.
5. As the Drain current decays linearly toward zero, proportional gate drive control reduces the Gate voltage so the MOSFET can be turned off rapidly at zero current crossing. The GATE voltage is removed when the Drain-Source voltage crosses the detection threshold voltage to minimize reverse current flow.
6. At zero Drain current, the controller GATE output voltage is pulled low to  $V_{G(off)}$  to ensure that the MOSFET is off.

Figure 4 shows typical operating waveforms for ZXGD3103 driving a MOSFET with  $Q_{g(TOT)} = 82\text{nC}$  in a Flyback converter operating in critical conduction mode.

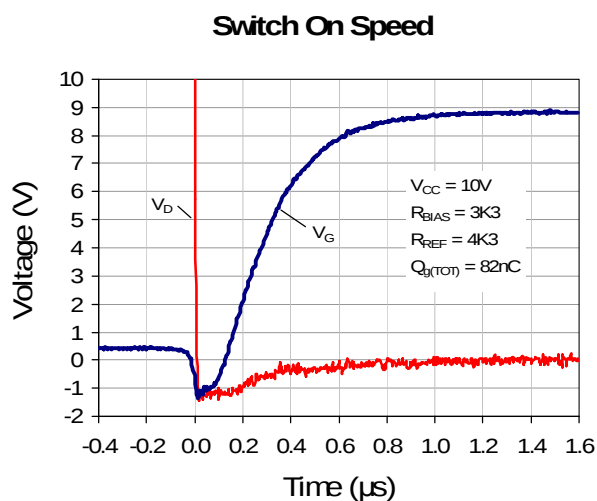


**Figure 3. Timing diagram for a critical conduction mode Flyback converter**

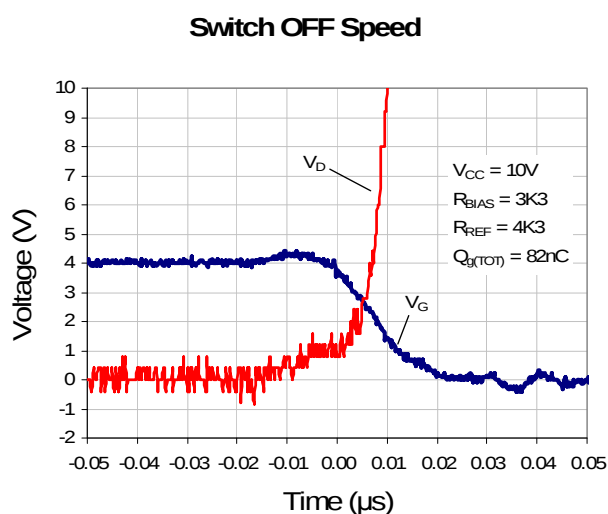
## Typical waveforms



**Fig 4a: Critical conduction mode**



**Fig 4b: Typical switch ON speed when driving a  $Q_{g(TOT)} = 82\text{nC}$  MOSFET**



**Fig 4c: Typical switch OFF speed when driving a  $Q_{g(TOT)} = 82\text{nC}$  MOSFET**

## Design considerations

It is advisable to decouple the ZXGD3103 closely to  $V_{CC}$  and ground due to the possibility of high peak gate currents with a  $1\mu\text{F}$  X7R type ceramic capacitor as shown in Figure 2. The Gate pins should be as close to the MOSFET's gate as possible. Also the ground return loop should be as short as possible.

To minimize parasitic inductance-induced premature turn-off issue of the synchronous controller always keep the PCB track length between ZXGD3101's Drain input and MOSFET's Drain to less than 10mm. Low internal inductance MOSFET packages such as SO-8 and PolarPak are also recommended for high switching frequency power conversion to minimize body diode conduction.

R1, Q1 D1 and C1 in Figure 1 are only required as a series drop-down regulator to maintain a stable  $V_{CC}$  around 10V from a power supply output voltage greater than 15V.

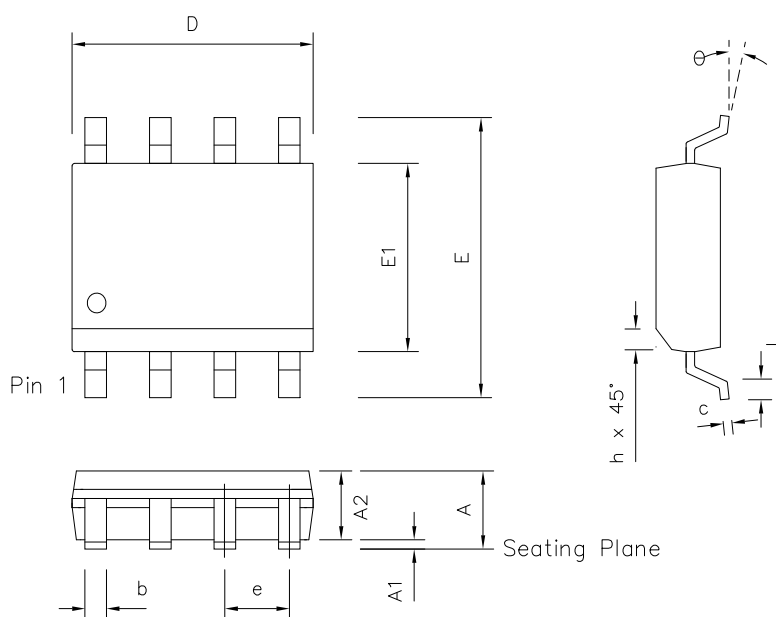
External gate resistors are optional. They can be inserted to control the rise and fall time which may help with EMI issues.

The proper selection of external resistors  $R_{REF}$  and  $R_{BIAS}$  is important to the optimum device operation. Select a value for resistor  $R_{REF}$  and  $R_{BIAS}$  from Table 1 based on the desired  $V_{CC}$  value. This provides the typical ZXGD3103's detection threshold voltage of 10mV.

**Table 1. Recommended resistor values for various supply voltages**

| $V_{CC}$ | $R_{BIAS}$ | $R_{REF}$ |
|----------|------------|-----------|
| 5V       | 1K6        | 2K0       |
| 10V      | 3K3        | 4K3       |
| 12V      | 3K9        | 5K1       |
| 15V      | 5K1        | 6K8       |

## Package Outline and Dimensions



|                      | Min<br>mm | Max<br>mm |
|----------------------|-----------|-----------|
| A                    | —         | 1.75      |
| A1                   | 0.08      | 0.25      |
| A2                   | 1.30      | 1.50      |
| D                    | 4.80      | 5.30      |
| E                    | 5.79      | 6.20      |
| E1                   | 3.70      | 4.10      |
| L                    | 0.38      | 1.27      |
| e                    | 1.27 TYP  |           |
| b                    | 0.30      | 0.50      |
| O                    | 0°        | 8°        |
| h                    | —         | 0.35      |
| All dimensions in mm |           |           |

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